

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("20020084747").PN.	US-PGPUB; USPAT; USOCR; JPO; DERWENT	OR	OFF	2003/07/31 14:41
S2	5653	(insulator insulating) and electrode and (transparent ITO) and reflecting	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2003/07/31 13:31
S3	1457	(TFT or (thin adj film adj transistor)) and (insulator insulating) and electrode and (transparent ITO) and reflecting	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2003/07/31 13:32
S4	44	"5341012".URPN.	USPAT	OR	ON	2003/07/31 14:38
S5	1	("20030083544").PN.	US-PGPUB; USPAT; USOCR; JPO; DERWENT	OR	OFF	2003/07/31 16:05
S6	7	((("6583456") or ("6407418") or ("6593689") or ("20020158588")).PN.	US-PGPUB; USPAT; USOCR; JPO; DERWENT	OR	OFF	2003/07/31 16:24
S7	3	("6034406" "6051857" "6069376").PN.	USPAT	OR	ON	2003/07/31 16:16
S8	34	"5408345".URPN.	USPAT	OR	ON	2003/07/31 16:23
S9	71	((313/506,499,503,504).CCLS.) and (TFT or (thin adj film adj transistor)) and (transparent ITO) and (reflecting reflect)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2003/07/31 16:26
S10	8	("5643826" "5711824" "5834893" "5882761" "5891264" "5923962" "6056614" "6242290").PN.	USPAT	OR	ON	2003/08/01 09:47
S11	25	"5834893".URPN.	USPAT	OR	ON	2003/08/01 09:49
S12	8	("5643826" "5711824" "5834893" "5882761" "5891264" "5923962" "6056614" "6242290").PN.	USPAT	OR	ON	2003/08/01 09:57
S13	15	("4356429" "4670689" "4908603" "4950950" "5122711" "5291098" "5294870" "5427858" "5505985" "5529853" "5552678" "5663573" "5674597" "5674635" "5681664").PN.	USPAT	OR	ON	2003/08/01 10:32

S14	7	("3172862" "3173050" "3227656" "3530325" "3621321" "3995299" "4164431").PN.	USPAT	OR	ON	2003/08/01 10:33
S15	94	"5616506".URPN.	USPAT	OR	ON	2003/08/01 11:15
S16	170	(TFT or (thin adj film adj transistor)) and (insulator insulating) and electrode and (transparent ITO) and reflecting and luminous	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2003/08/01 11:39
S17	63	((TFT or (thin adj film adj transistor)) and (insulator insulating) and electrode and (transparent ITO) and reflecting and luminous) and (gate same (transparent ITO))	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2003/08/01 11:39
S18	3	((TFT or (thin adj film adj transistor)) and (insulator insulating) and electrode and (transparent ITO) and reflecting and luminous) and (gate near3 (transparent ITO))	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2003/08/01 11:39
S19	151	MgO with (electrode anode cathode) with transparent	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/01/29 11:44
S20	2660	(313/506,499,503,504).CCLS.	US-PGPUB; USPAT; USOCR; JPO; DERWENT	OR	OFF	2004/01/29 12:57
S21	0	(MgO with (electrode anode cathode) with transparent) and ((313/506,499,503,504).CCLS.)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/01/29 11:45
S22	78	(MgO with (electrode anode cathode) with transparent) and ("313"/\$)".ccls"	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/01/29 11:45
S23	297	(313/506,499,503,504).ccls. and (@pd > "20030903")	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 16:24
S24	201	((313/506,499,503,504).ccls. and (@pd > "20030903")) and (TFT (thin adj film))	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/01/29 14:03
S25	59	((313/506,499,503,504).CCLS.) and (circ\$4 near pixels)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 16:32

S26	38	macchiarolo.xa.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 16:18
S27	813	(313\$).ccls. and (TFT (thin adj film adj transistor)) and (open\$4 hole aperture slit slot gap passage passageway rift breach fissure separation)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 16:31
S28	481	((313/506,499,503,504).CCLS.) and ((313\$).ccls. and (TFT (thin adj film adj transistor)) and (open\$4 hole aperture slit slot gap passage passageway rift breach fissure separation))	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 17:08
S29	6124	((313/506,499,503,504) (257/98-100)).CCLS.)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 17:09
S30	665	((313/506,499,503,504) (257/98-100)).CCLS.) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 17:11
S31	653	((313/506,499,503,504) (257/98-100)).CCLS.) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)) and (open\$4 hole aperture slit slot gap passage passageway rift fissure separation)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 17:11
S32	620	((313/506,499,503,504) (257/98-100)).CCLS.) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)) and (open\$4 hole aperture slit slot gap passage passageway rift fissure separation) same (electrode anode cathode)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2004/08/11 17:12
S33	2	("20010017517").PN.	US-PGPUB; USPAT; USOCR; JPO; DERWENT	OR	OFF	2004/08/11 17:33
S34	4	("5550066") or ("6346717") or ("6630784") or ("5895692")).PN.	USPAT; USOCR	OR	OFF	2004/08/11 17:35

S35	273	(((((313/506,499,503,504) (257/98-100)).CCLS.)) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)) and ((open\$4 hole aperture slit slot gap passage passageway rift fissure separation) same (electrode anode cathode))	USPAT	OR	ON	2004/08/12 13:17
S36	82	(((((257/88-97)).CCLS.)) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)) and ((open\$4 hole aperture slit slot gap passage passageway rift fissure separation) same (electrode anode cathode))	US-PGPUB; USPAT	OR	ON	2004/08/12 13:18
S37	57	(((((257/88-97)).CCLS.)) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)) and ((open\$4 hole aperture slit slot gap passage passageway rift fissure separation) same (electrode anode cathode))) not ((((((313/506,499,503,504) (257/98-100)).CCLS.)) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)) and ((open\$4 hole aperture slit slot gap passage passageway rift fissure separation) same (electrode anode cathode)))	US-PGPUB; USPAT	OR	ON	2004/08/12 13:19
S38	9	"5585695".URPN.	USPAT	OR	ON	2004/08/12 17:37
S39	273	(((((313/506,499,503,504) (257/98-100)).CCLS.)) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)) and (open\$4 hole aperture slit slot gap passage passageway rift fissure separation) same (electrode anode cathode)	USPAT	OR	ON	2004/08/12 17:41

S40	10	(((313/506,499,503,504) (257/88-100)).CCLS.)) and (TFT (active near3 matrix) (thin near3 film near3 transistor)) and (EL electroluminescen\$3 luminous fluorescent) with (layer element film member)) and (circular circle round\$2 ring\$shap\$2 ring oval curv\$3 crescent) near2 (electrode anode cathode)	USPAT	OR	ON	2004/08/12 17:44
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